**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V	
$V_{GS}$	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	0.8	Α	
Static charac	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 25 °C		-	300	380	mΩ	

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV450ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV450ENEA	DZ%

[1] % = placeholder for manufacturing site code

## **Limiting values**

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit		
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V		
$V_{GS}$	gate-source voltage			-20	20	V		
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	0.8	Α		
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	0.5	Α		
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	3.2	Α		
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.14 A; DUT in avalanche (unclamped)		-	4.2	mJ		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	323	mW		
			[1]	-	466	mW		
		$T_{sp} = 25  ^{\circ}C$		-	554	mW		
T <sub>j</sub>	junction temperature			-55	150	°C		
T <sub>amb</sub>	ambient temperature			-55	150	°C		
T <sub>stg</sub>	storage temperature			-65	150	°C		
Source-drain diode								
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.7	Α		
ESD Maximum rating								
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V		

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $6~{\rm cm}^2$ . Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

Measured between all pins.

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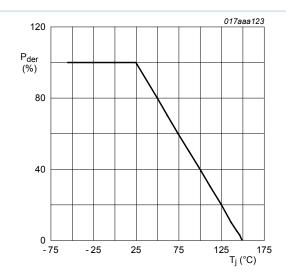


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

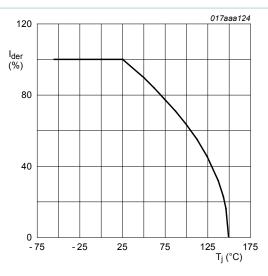


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

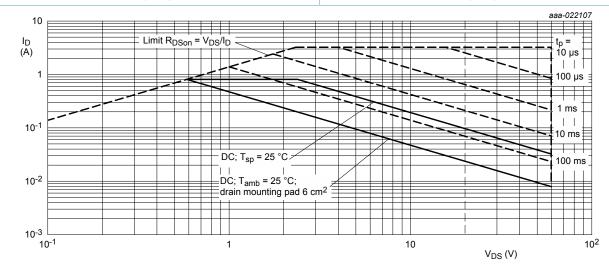


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	337	387	K/W
			[2]	-	233	268	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	57	66	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

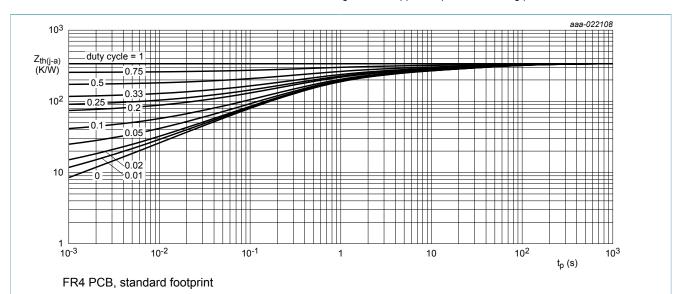


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

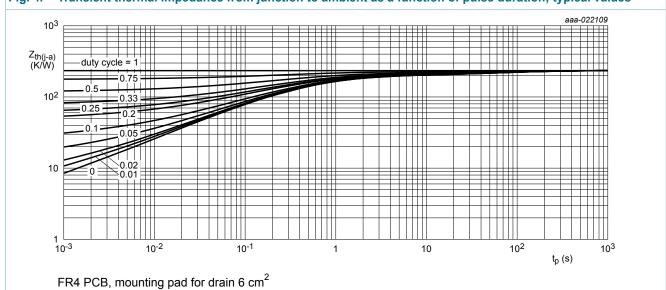


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 25 °C	-	300	380	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 150 °C	-	574	727	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 0.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	332	440	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_D$ = 0.9 A; $T_j$ = 25 °C	-	3.5	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	13	-	Ω
Dynamic c	haracteristics	1				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; I_{D} = 0.9 \text{ A}; V_{GS} = 10 \text{ V};$	-	2.4	3.6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.3	-	nC
$Q_{GD}$	gate-drain charge		-	0.4	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	101	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	10	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 0.9 \text{ A}; V_{GS} = 10 \text{ V};$	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	10	-	ns
t <sub>f</sub>	fall time		-	3	-	ns
Source-dra	in diode	1	1			
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 0.7 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V

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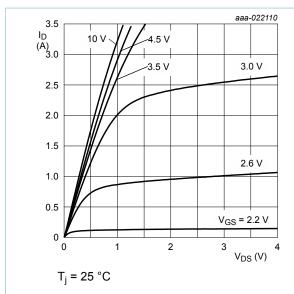


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

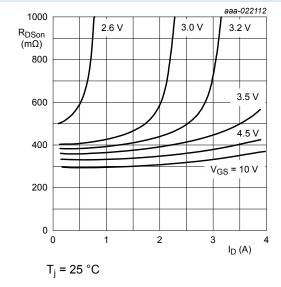


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

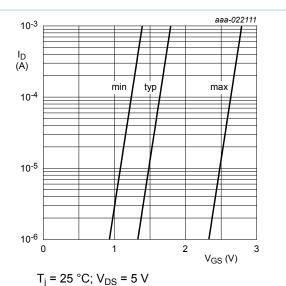


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

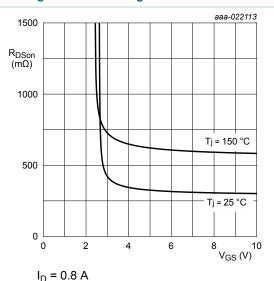


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, N-channel Trench MOSFET

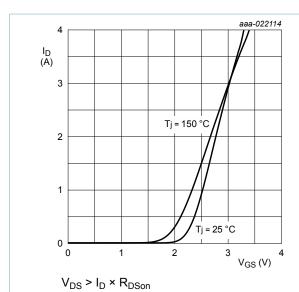


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

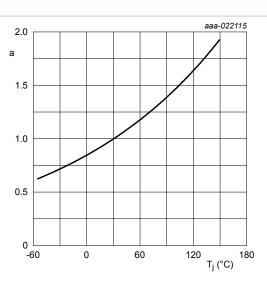


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

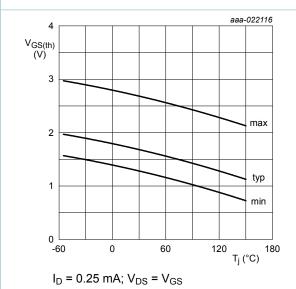
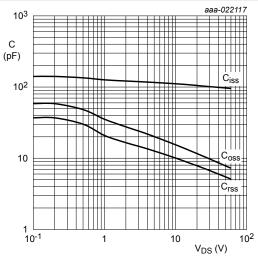


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 60 V, N-channel Trench MOSFET

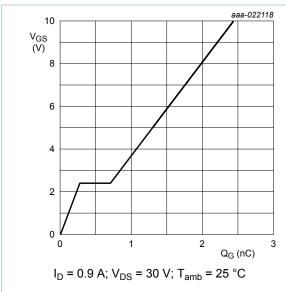


Fig. 14. Gate-source voltage as a function of gate charge; typical values

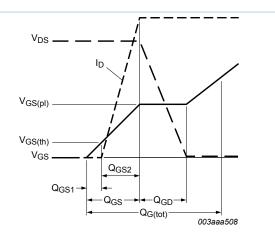


Fig. 15. MOSFET transistor: Gate charge waveform definitions

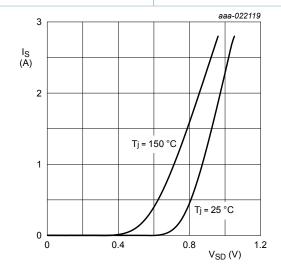


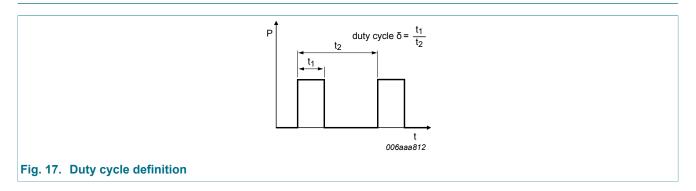
Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

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## 11. Test information

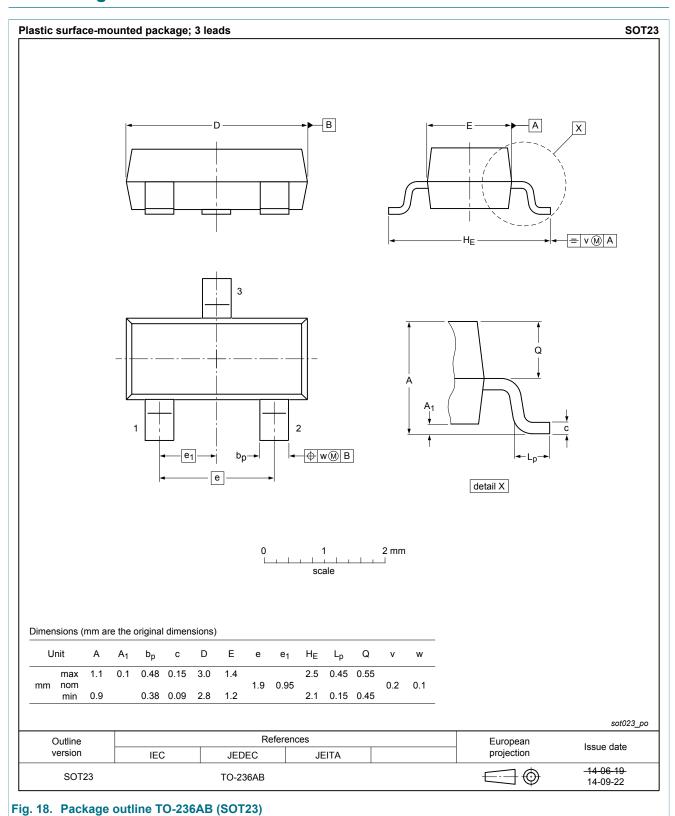


## 11.1 Quality information

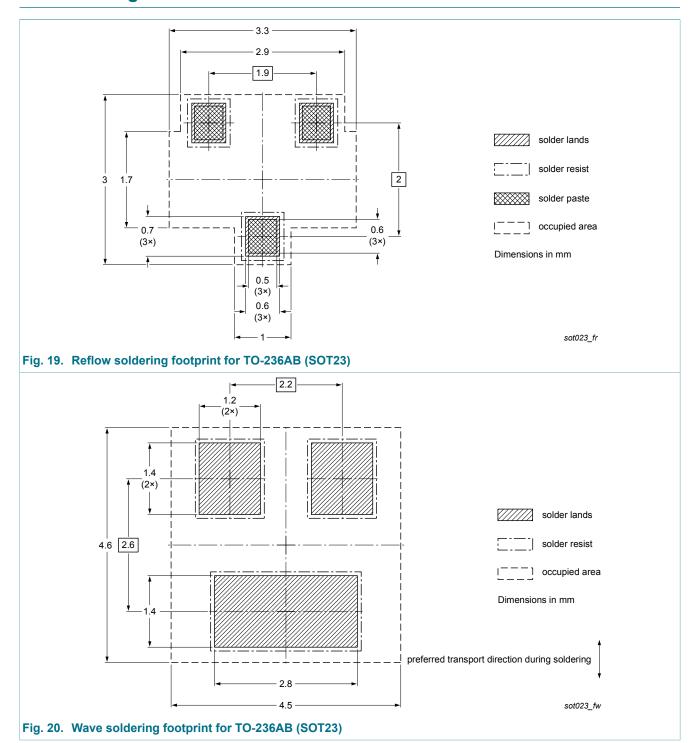
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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## 12. Package outline



## 13. Soldering



**60 V, N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV450ENEA v.1	20160323	Product data sheet	-	-

#### 60 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### **60 V, N-channel Trench MOSFET**

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